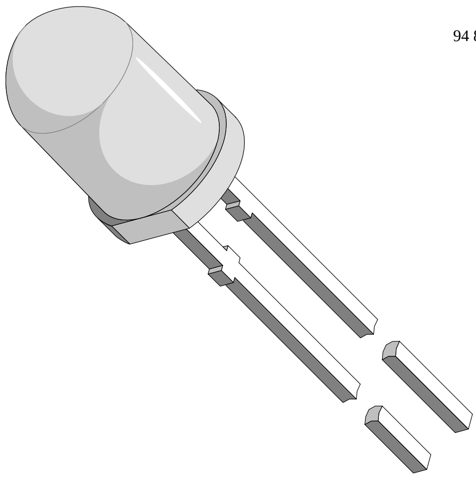
High Efficiency LED, ø 5 mm Untinted Non-Diffused

Color	Type	Technology	Angle of Half Intensity ±φ
Yellow	TLHY5800	GaAsP on GaP	4°
Green	TLHG5800	GaP on GaP	4°
Pure green	TLHP5800	GaP on GaP	4°

Description

The TLH.5800 series was developed for standard applications which need a very small radiation angle or a very high luminous intensity.
It is housed in a 5 mm untinted non-diffused plastic package. The very small viewing angle of these devices provide a very high luminous intensity.
The yellow and green LEDs are categorized in luminous intensity and additionally in wavelength groups.
That allows users to assemble LEDs with uniform appearance.



Features

- Standard T-1¾ package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very small viewing angle
- Very high intensity
- Luminous intensity categorized
- Yellow and green color categorized

Applications

Status lights
OFF / ON indicator
Lightpipe
Outdoor display
Medical instruments
Maintenance lights
Legend lights

Absolute Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

TLHY5800 ,TLHG5800 ,TLHP5800 ,

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
DC forward current	$T_{amb} \leq 65°C$	I_F	30	mA
Surge forward current	$t_p \leq 10\ \mu s$	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 65°C$	P_V	100	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	–20 to +100	°C
Storage temperature range		T_{stg}	–55 to +100	°C
Soldering temperature	t ≤ 5 s, 2 mm from body	T_{sd}	260	°C
Thermal resistance junction/ambient		R_{thJA}	350	K/W

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Yellow (TLHY5800)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	I_F = 20 mA, $I_{Vmin}/I_{Vmax} \geq 0.5$		I_V	100	250		mcd
Dominant wavelength	I_F = 10 mA		λ_d	581		594	nm
Peak wavelength	I_F = 10 mA		λ_p		585		nm
Angle of half intensity	I_F = 10 mA		φ		±4		deg
Forward voltage	I_F = 20 mA		V_F		2.4	3	V
Reverse voltage	I_R = 10 μA		V_R	6	15		V
Junction capacitance	V_R = 0, f = 1 MHz		C_j		50		pF

Green (TLHG5800)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	I_F = 20 mA, $I_{Vmin}/I_{Vmax} \geq 0.5$		I_V	400	700		mcd
Dominant wavelength	I_F = 10 mA		λ_d	562		575	nm
Peak wavelength	I_F = 10 mA		λ_p		565		nm
Angle of half intensity	I_F = 10 mA		φ		±4		deg
Forward voltage	I_F = 20 mA		V_F		2.4	3	V
Reverse voltage	I_R = 10 μA		V_R	6	15		V
Junction capacitance	V_R = 0, f = 1 MHz		C_j		50		pF

Pure green (TLHP5800)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	I_F = 20 mA, $I_{Vmin}/I_{Vmax} \geq 0.5$		I_V	25	85		mcd
Dominant wavelength	I_F = 10 mA		λ_d	555		565	nm
Peak wavelength	I_F = 10 mA		λ_p		555		nm
Angle of half intensity	I_F = 10 mA		φ		±4		deg
Forward voltage	I_F = 20 mA		V_F		2.4	3	V
Reverse voltage	I_R = 10 μA		V_R	6	15		V
Junction capacitance	V_R = 0, f = 1 MHz		C_j		50		pF

Typical Characteristics (T_{amb} = 25°C, unless otherwise specified)

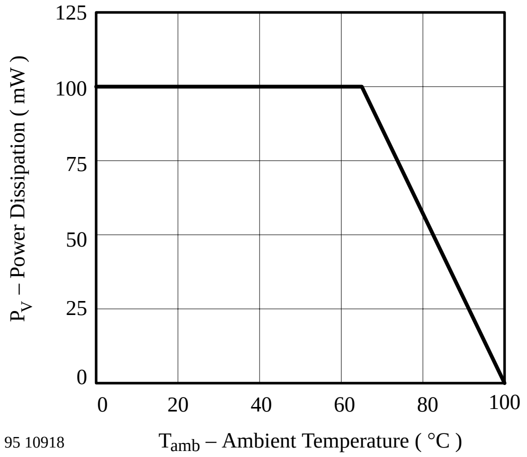


Figure 1 Power Dissipation vs. Ambient Temperature

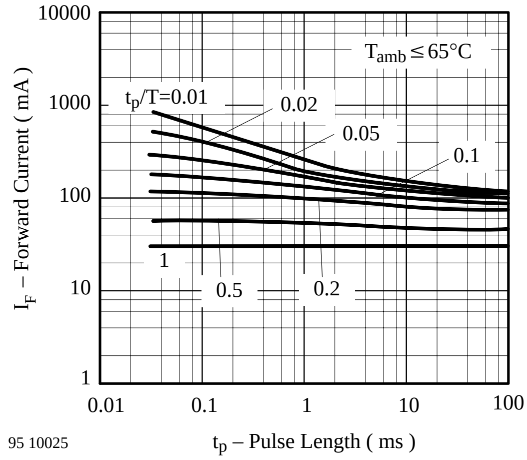


Figure 3 Forward Current vs. Pulse Length

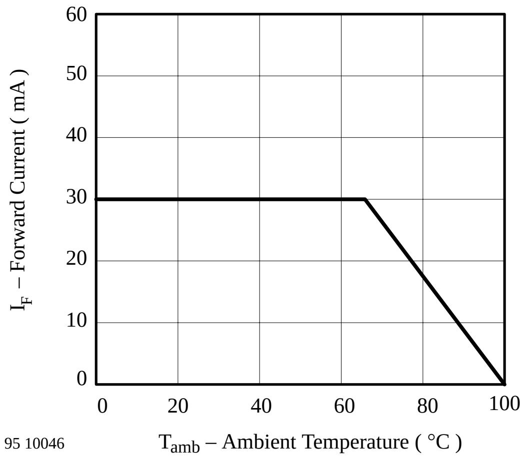


Figure 2 Forward Current vs. Ambient Temperature

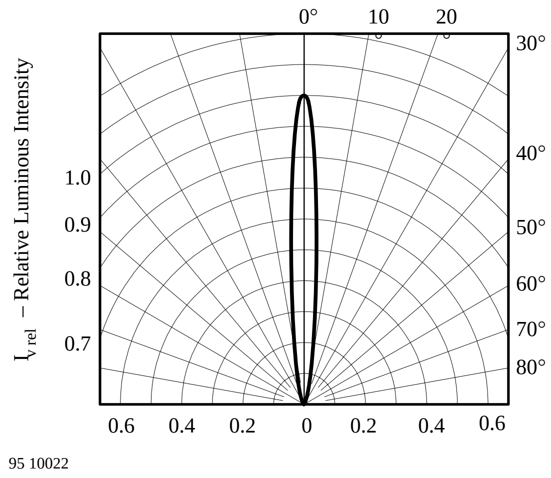


Figure 4 Rel. Luminous Intensity vs. Angular Displacement

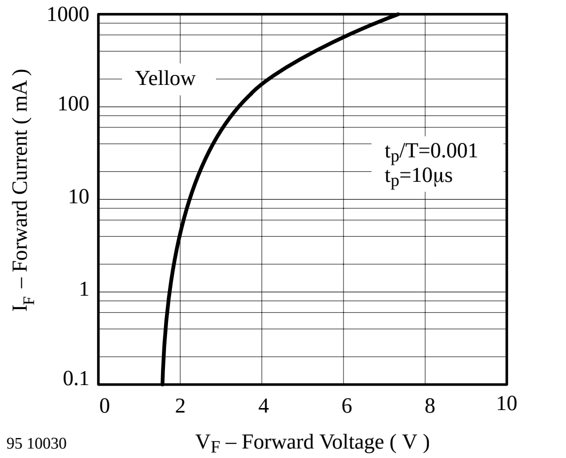


Figure 5 Forward Current vs. Forward Voltage

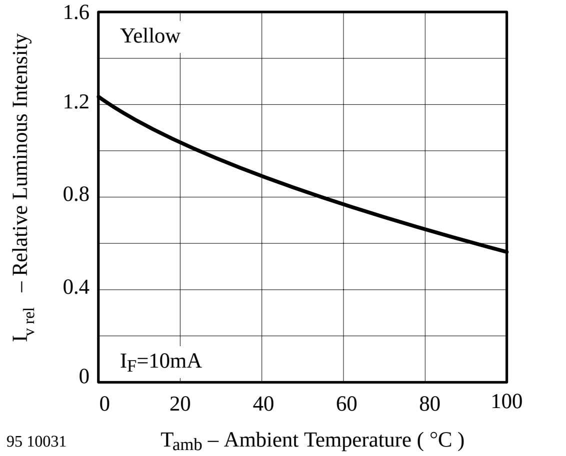


Figure 6 Rel. Luminous Intensity vs. Ambient Temperature

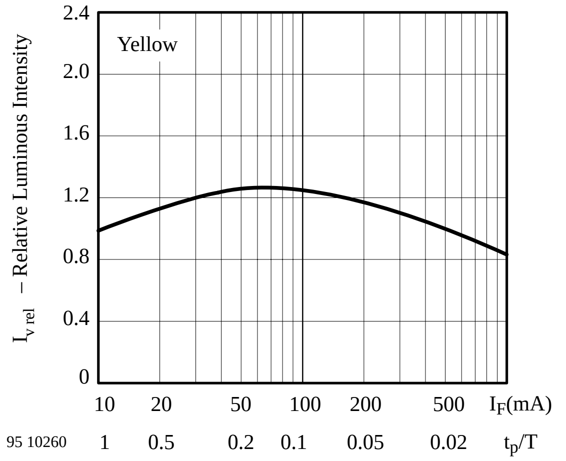


Figure 7 Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

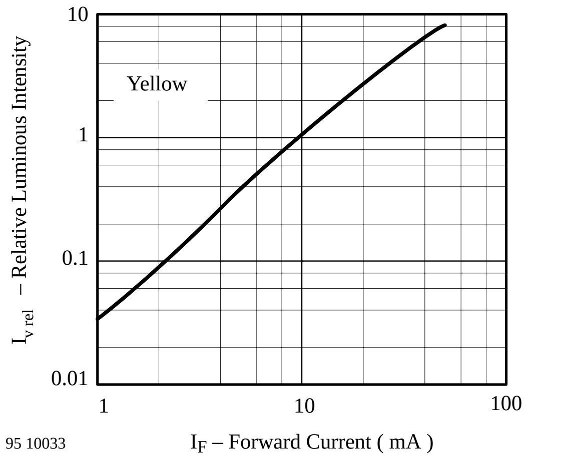


Figure 8 Relative Luminous Intensity vs. Forward Current

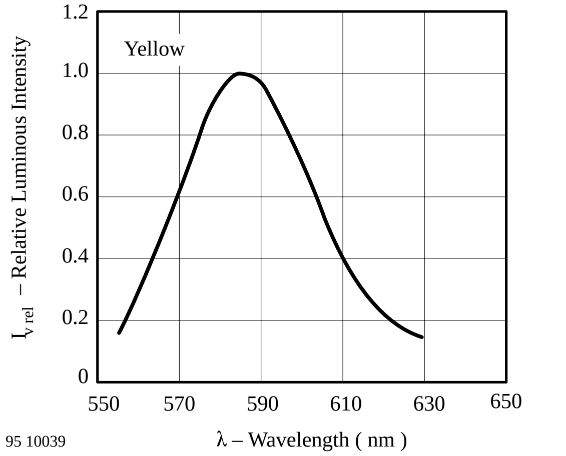


Figure 9 Relative Luminous Intensity vs. Wavelength

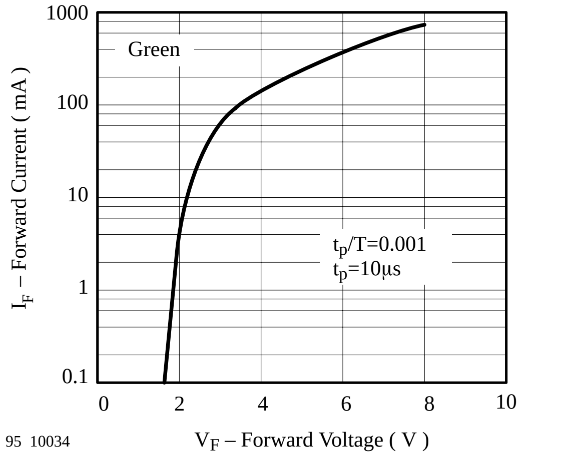


Figure 10 Forward Current vs. Forward Voltage

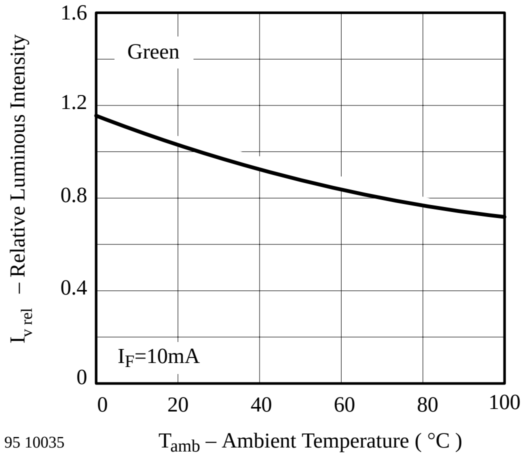


Figure 11 Rel. Luminous Intensity vs. Ambient Temperature

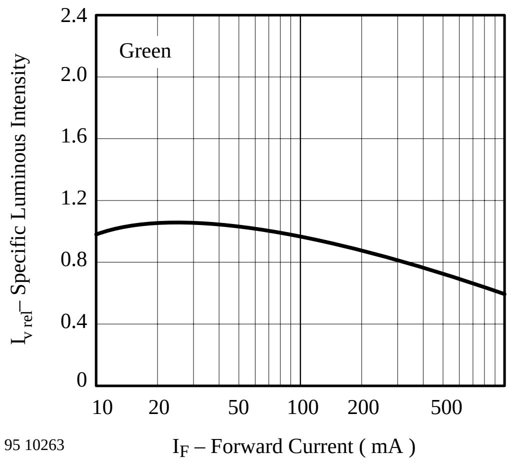


Figure 12 Specific Luminous Intensity vs. Forward Current

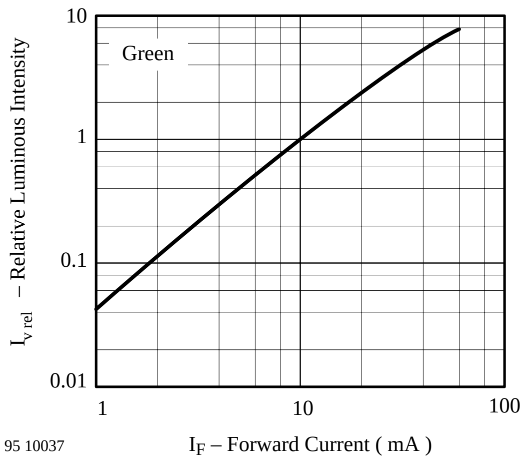


Figure 13 Relative Luminous Intensity vs. Forward Current

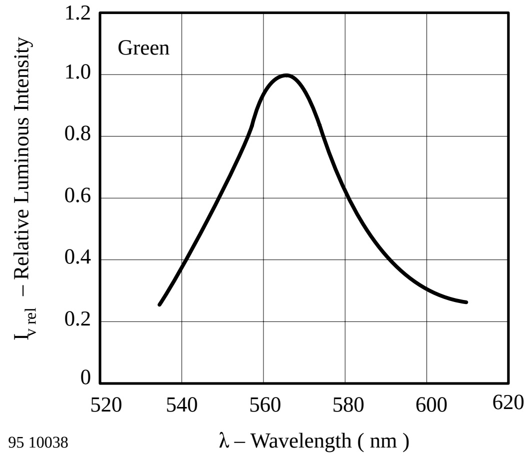


Figure 14 Relative Luminous Intensity vs. Wavelength

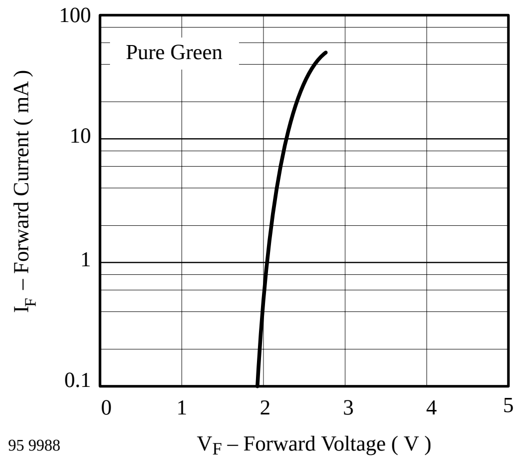


Figure 15 Rel. Luminous Intensity vs. Ambient Temperature

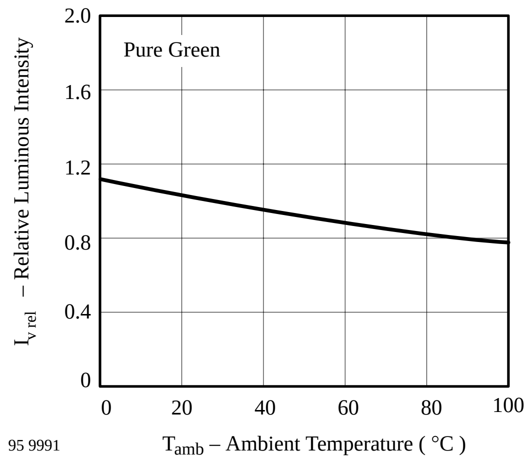


Figure 16 Rel. Luminous Intensity vs. Ambient Temperature

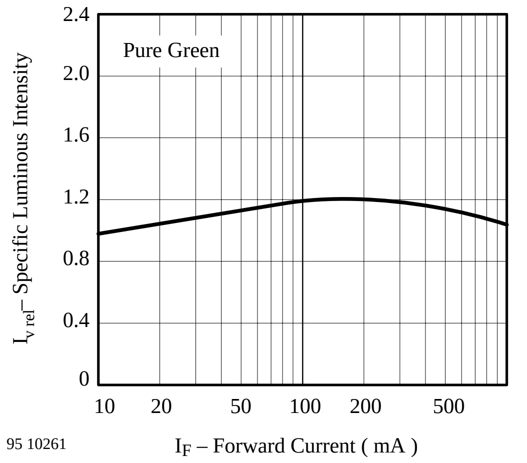


Figure 17 Specific Luminous Intensity vs. Forward Current

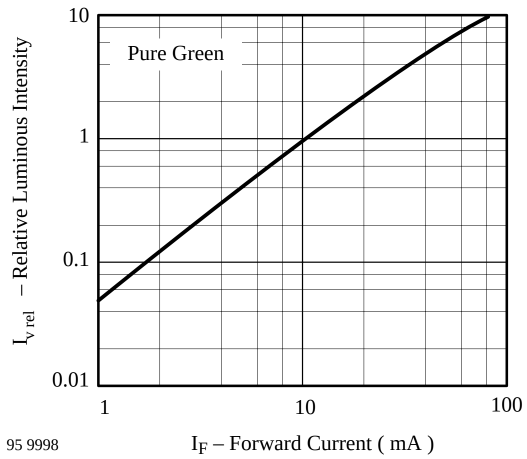


Figure 18 Relative Luminous Intensity vs. Forward Current

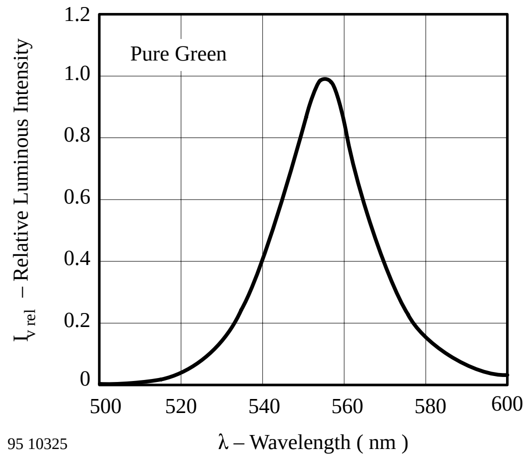
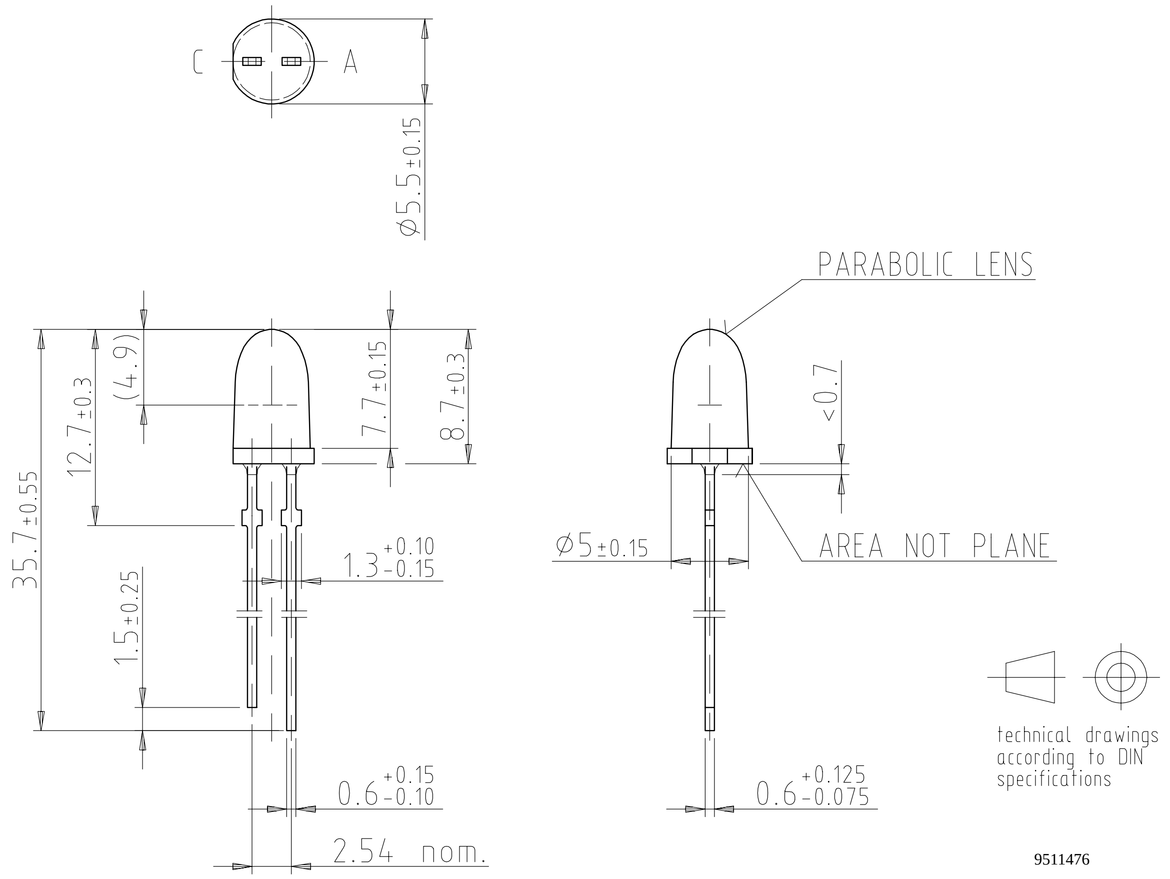


Figure 19 Relative Luminous Intensity vs. Wavelength

Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively

2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA

3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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Данный компонент на территории Российской Федерации

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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